

Search Notes

L Number	Hits	Search Text	DB	Time stamp
-	0	upstanding adj pillar same etch\$3 and gate and pore	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/15 00:12
-	0	upstanding adj pillar and etch\$3 and gate and pore	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/15 00:12
-	224	upstanding adj pillar	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/15 00:12
-	19	upstanding adj pillar and etch\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/15 00:13
-	8	upstanding adj pillar and etch\$3 and gate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/15 00:14
-	17	upstanding with pillar and etch\$3 and gate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/15 00:15
-	62	pillar and etch\$3 and gate and pore	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/15 00:29
-	3	pillar and etch\$3 and gate same pore	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/15 00:31
-	5	pillar and gate same pore	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/15 00:32
-	218	channel and gate same pore	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/15 00:33
-	102	channel and gate with pore	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/15 00:36
-	5	channel and gate with pore and stack	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/15 00:36
-	69	pore same transistor and channel	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/11 22:20

-	3	pore same transistor and channel and gate and etch\$3 and pillar	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/06/11 22:41
-	555	(438/268).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/06/11 22:28
-	1684	(438/270).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/06/11 22:28
-	676	(257/382).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/06/11 22:28
-	288	(257/383).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/06/11 22:28
-	534	(257/302).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/06/11 22:28
-	796	(438/197).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/06/11 22:34
-	0	nanopillar and transistor and nanopore	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/06/11 22:35
-	1	nanopillar and transistor and nanopore	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/06/11 22:35
-	7	nanopillar and transistor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/06/11 22:37
-	52	pore same transistor and channel and gate and etch\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/06/11 22:41
-	3	pore same transistor and channel and gate and etch\$3 and pillar	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/06/11 22:41